

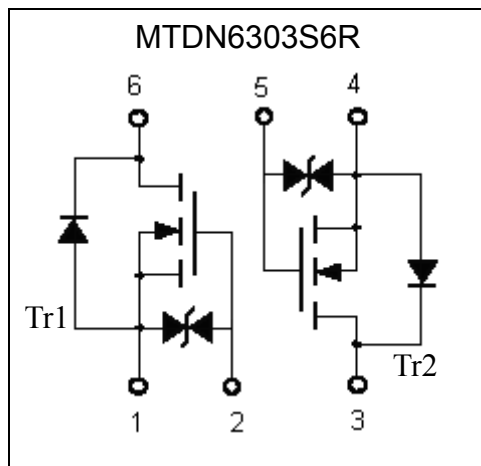
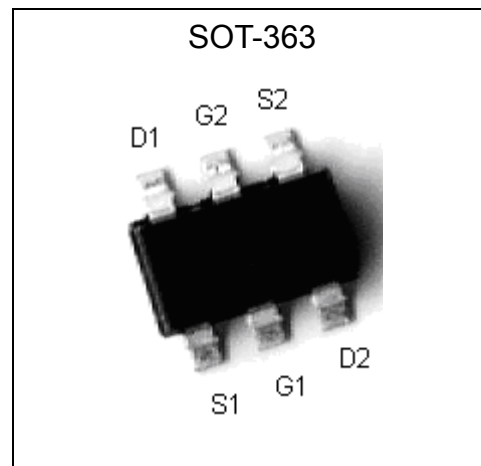
N-CHANNEL MOSFET (dual transistors)

MTDN6303S6R

BV _{DSS}	20V
I _D	760mA
R _{DS(on)} @V _{GS} =4.5V, I _D =600mA	370mΩ (typ)
R _{DS(on)} @V _{GS} =2.5V, I _D =400mA	500mΩ (typ)
R _{DS(on)} @V _{GS} =1.8V, I _D =350mA	1.1Ω (typ)

Features

- Low on-resistance
- High ESD capability
- High speed switching
- Low-voltage drive(1.8V)
- Pb-free lead plating and halogen-free package

Equivalent Circuit

Outline


The following characteristics apply to both Tr1 and Tr2

Absolute Maximum Ratings (Ta=25°C)

Parameter	Symbol	Limits	Unit	
Drain-Source Voltage	V _{DS}	20	V	
Gate-Source Voltage	V _{GS}	±8		
Continuous Drain Current @ T _A =25°C, V _{GS} =4.5V (Note 3)	I _D	760	mA	
Continuous Drain Current @ T _A =85°C, V _{GS} =4.5V (Note 3)		550		
Pulsed Drain Current (Notes 1, 2)	I _{DM}	3	A	
Maximum Power Dissipation (Note 3)	P _D	T _A =25°C	300	mW
		T _A =85°C	160	
ESD susceptibility		2000 (Note 4)	V	
Operating Junction and Storage Temperature	T _j , T _{stg}	-55~+150	°C	

- Note : 1. Pulse width limited by maximum junction temperature.
 2. Pulse width ≤ 300μs, duty cycle ≤ 2%.
 3. Surface mounted on 1 in² copper pad of FR-4 board, t ≤ 5s.
 4. Human body model, 1.5kΩ in series with 100pF



Thermal Performance

Parameter	Symbol	Limit	Unit
Thermal Resistance, Junction-to-Ambient(PCB mounted) (Note)	Rth,ja	417	°C/W

Note : Surface mounted on 1 in² copper pad of FR-4 board, t_≤5s.

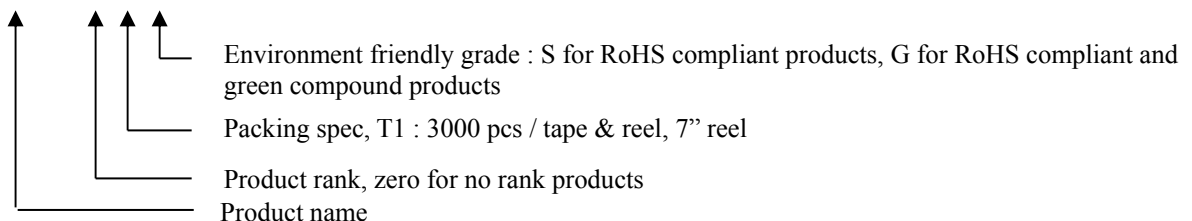
Electrical Characteristics (T_j=25°C, unless otherwise noted)

Symbol	Min.	Typ.	Max.	Unit	Test Conditions
Static					
B _V DSS	20	-	-	V	V _{GS} =0, I _D =250μA
ΔB _V DSS/ΔT _j	-	0.02	-	V/°C	Reference to 25°C, I _D =1mA
V _{GS(th)}	0.5	0.92	1.2	V	V _{DS} =V _{GS} , I _D =250μA
I _{GSS}	-	-	±10	μA	V _{GS} =±8V, V _{DS} =0
I _{DSS}	-	-	1		V _{DS} =20V, V _{GS} =0
	-	-	10	V _{DS} =16V, V _{GS} =0 (T _j =70°C)	
*R _{DS(ON)}	-	370	450	mΩ	V _{GS} =4.5V, I _D =600mA
	-	500	650		V _{GS} =2.5V, I _D =400mA
	-	1100	1300		V _{GS} =1.8V, I _D =350mA
*G _{FS}	-	1.4	-	S	V _{DS} =5V, I _D =600mA
Dynamic					
C _{iSS}	-	60	-	pF	V _{DS} =10V, V _{GS} =0, f=1MHz
C _{oSS}	-	14	-		
C _{rSS}	-	9	-		
t _{d(ON)}	-	4	-	ns	V _{DS} =10V, I _D =600mA, V _{GS} =10V R _G =3.3Ω, R _D =16.7Ω
t _r	-	10	-		
t _{d(OFF)}	-	15	-		
t _f	-	2	-		
Q _g	-	1.3	-	nC	V _{DS} =16V, I _D =600mA, V _{GS} =4.5V
Q _{gs}	-	0.3	-		
Q _{gd}	-	0.5	-		
Source-Drain Diode					
*V _{SD}	-	0.81	1.2	V	V _{GS} =0V, I _S =500mA

*Pulse Test : Pulse Width ≤300μs, Duty Cycle ≤2%

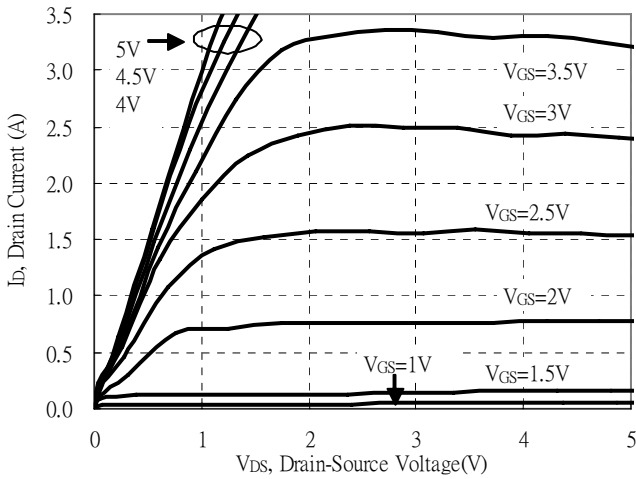
Ordering Information

Device	Package	Shipping
MTDN6303S6R-0-T1-G	SOT-363 (Pb-free lead plating and halogen-free package)	3000 pcs / tape & reel

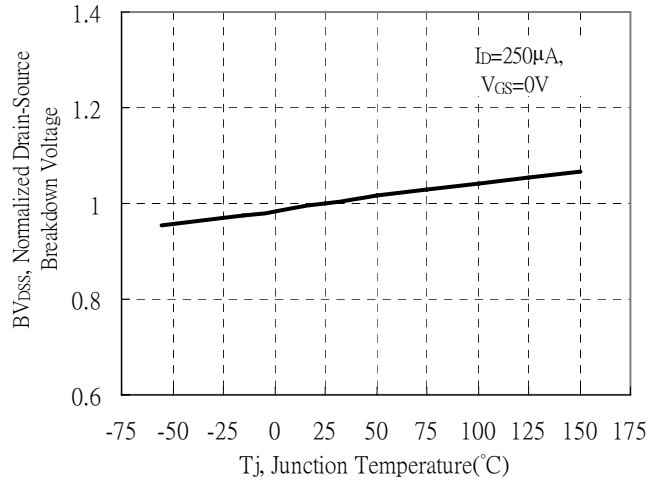


Typical Characteristics

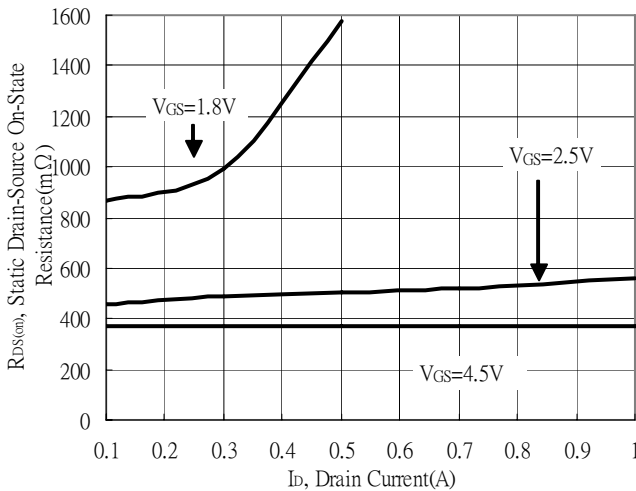
Typical Output Characteristics



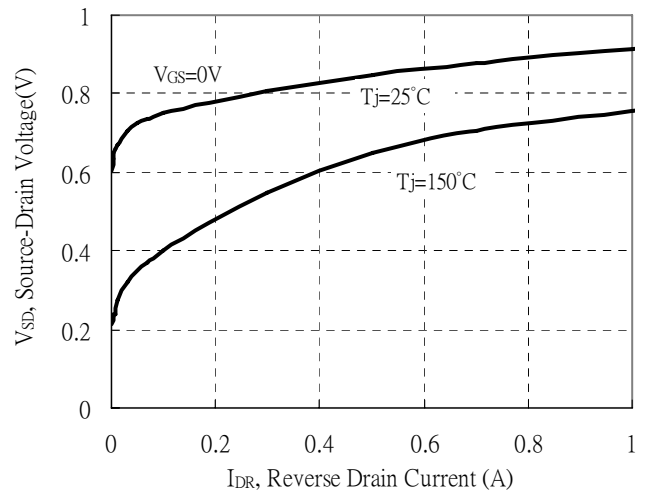
Breakdown Voltage vs Ambient Temperature



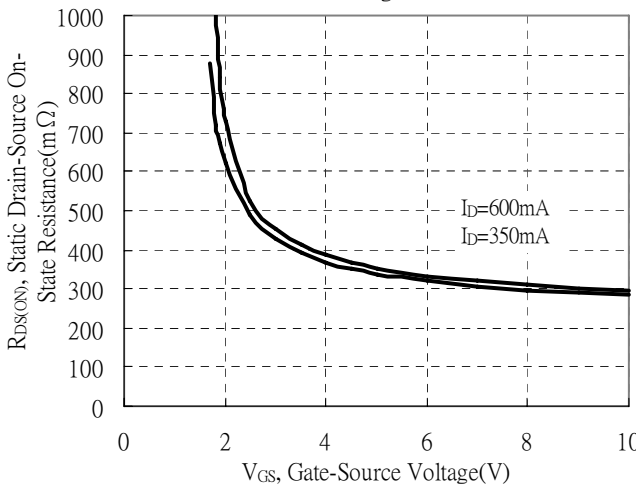
Static Drain-Source On-State resistance vs Drain Current



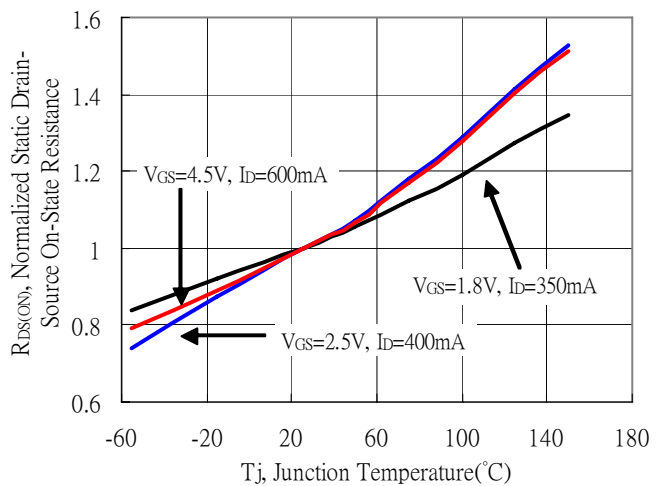
Reverse Drain Current vs Source-Drain Voltage



Static Drain-Source On-State Resistance vs Gate-Source Voltage

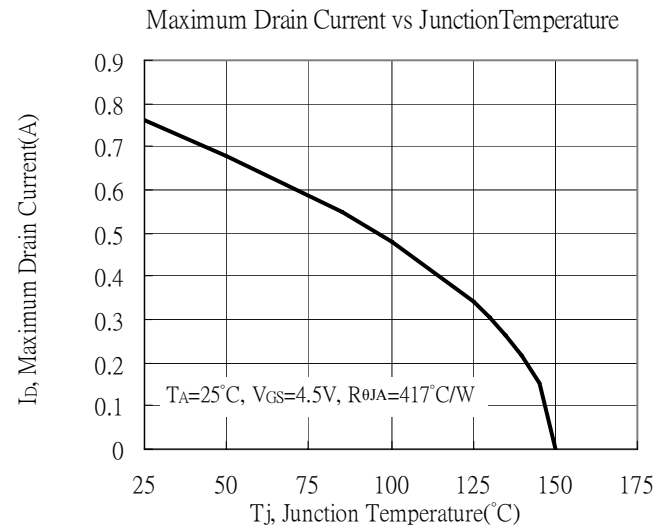
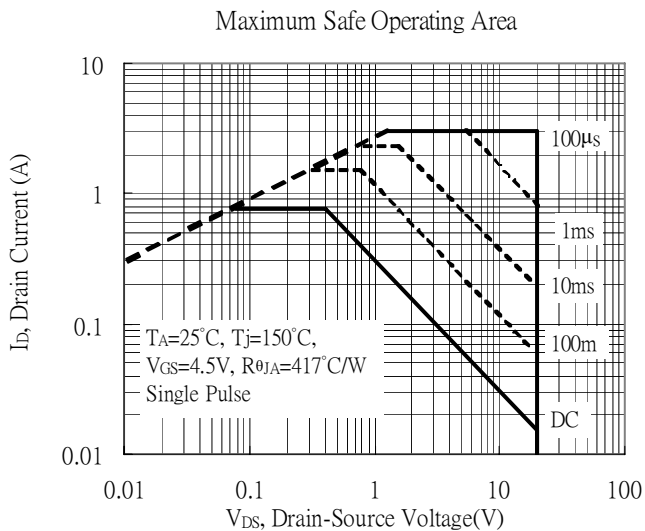
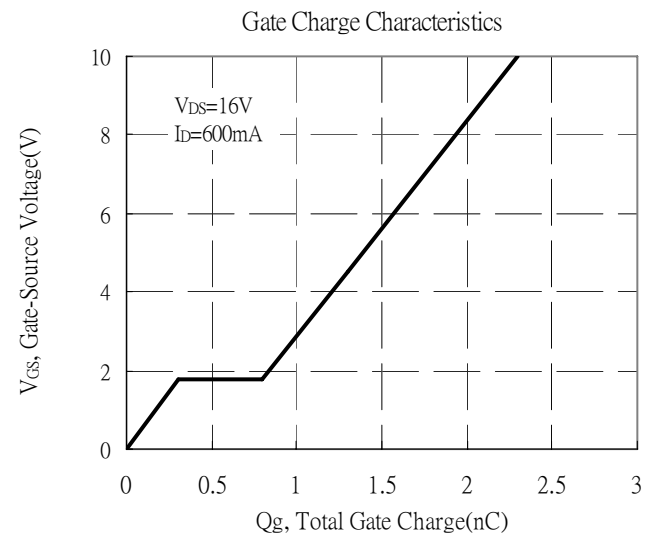
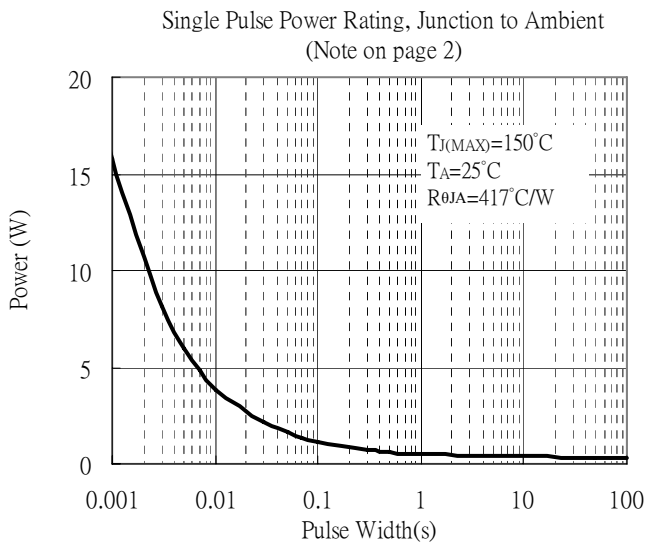
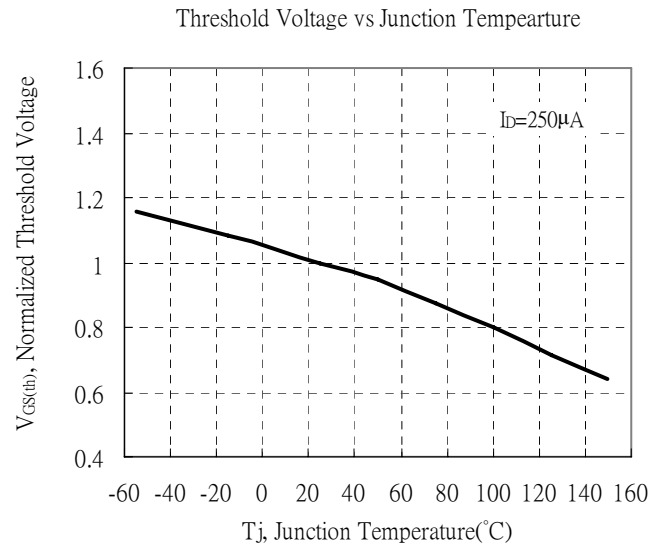
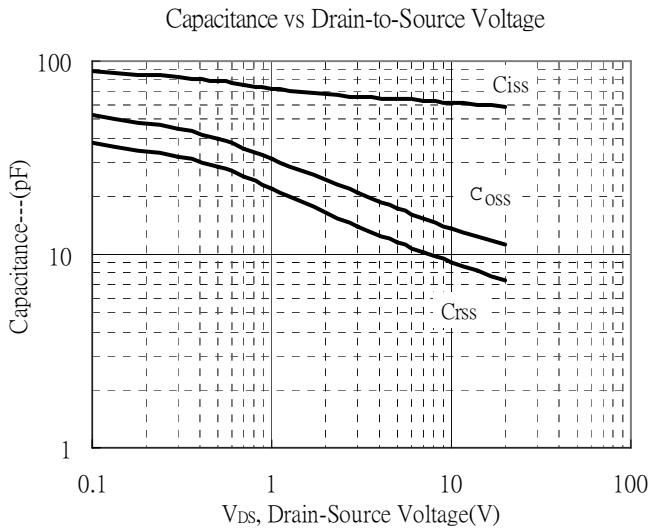


Drain-Source On-State Resistance vs Junction Temperature



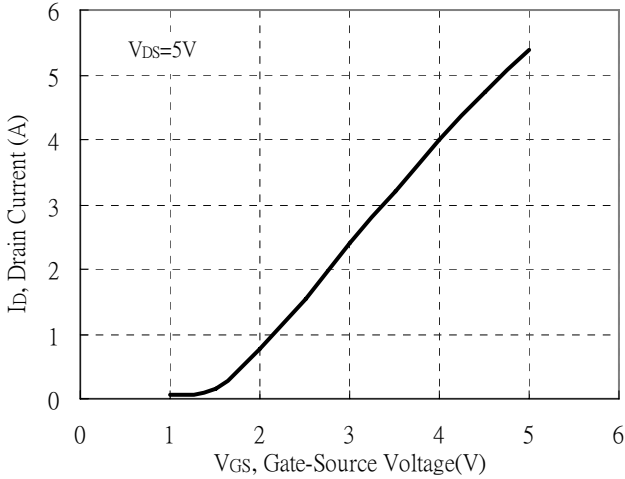


Typical Characteristics(Cont.)

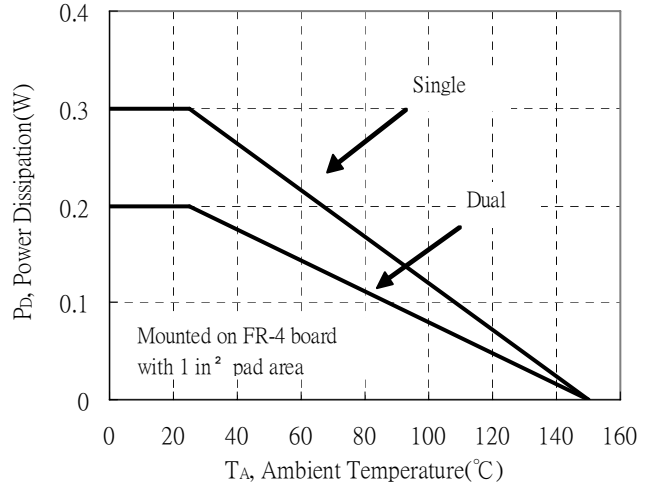


Typical Characteristics(Cont.)

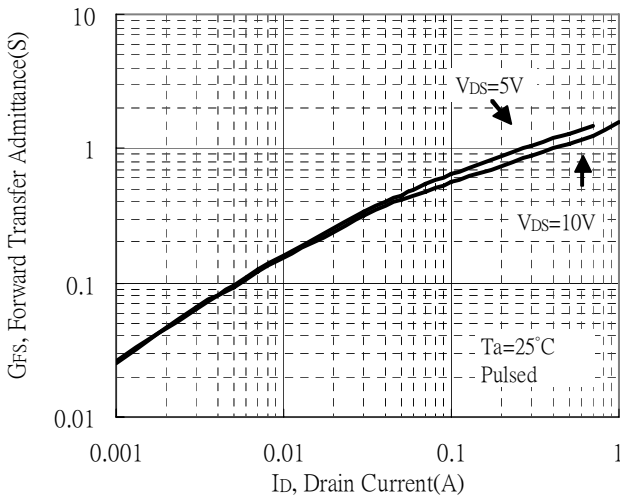
Typical Transfer Characteristics



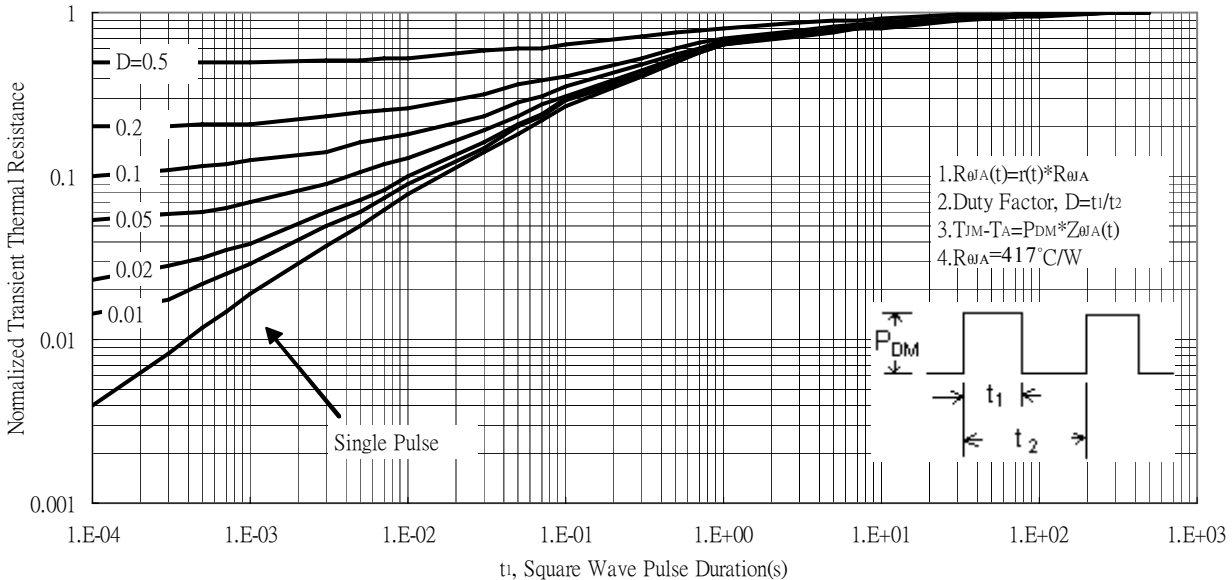
Power Derating Curve



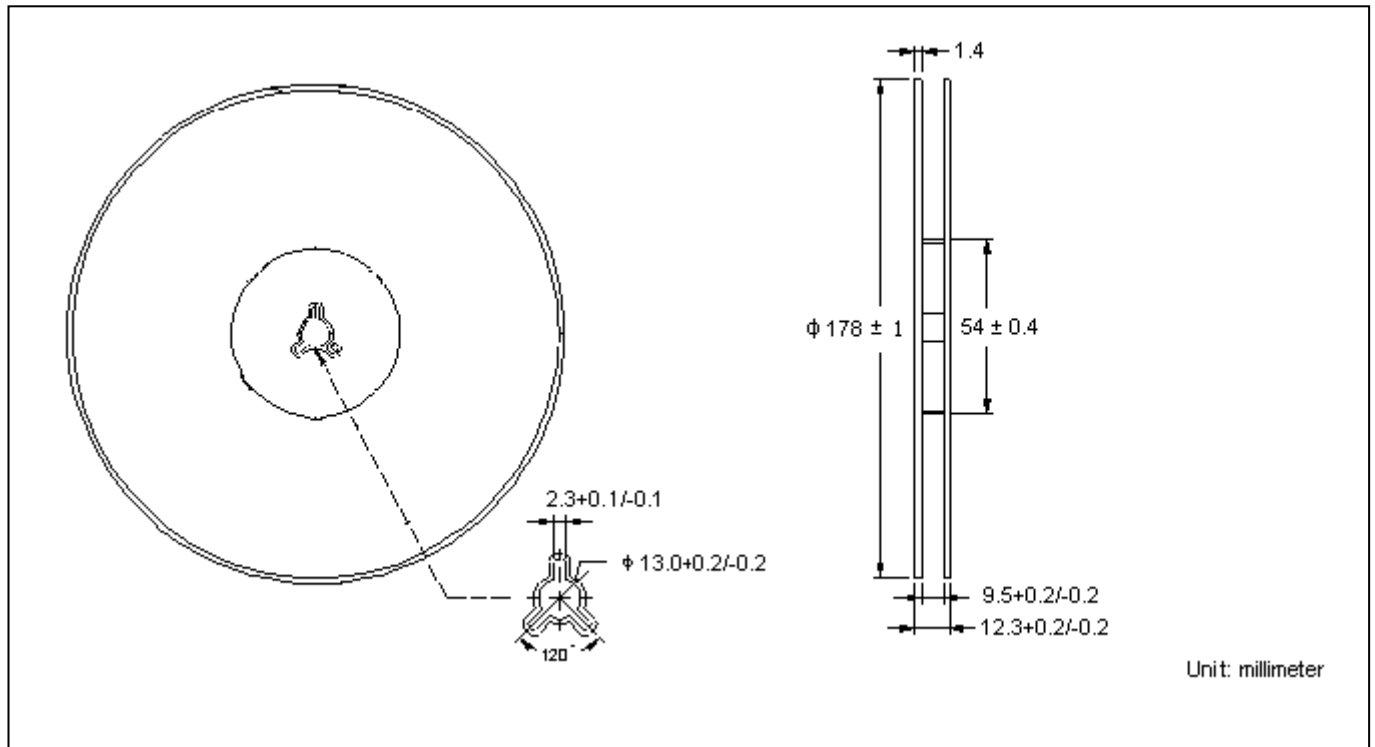
Forward Transfer Admittance vs Drain Current



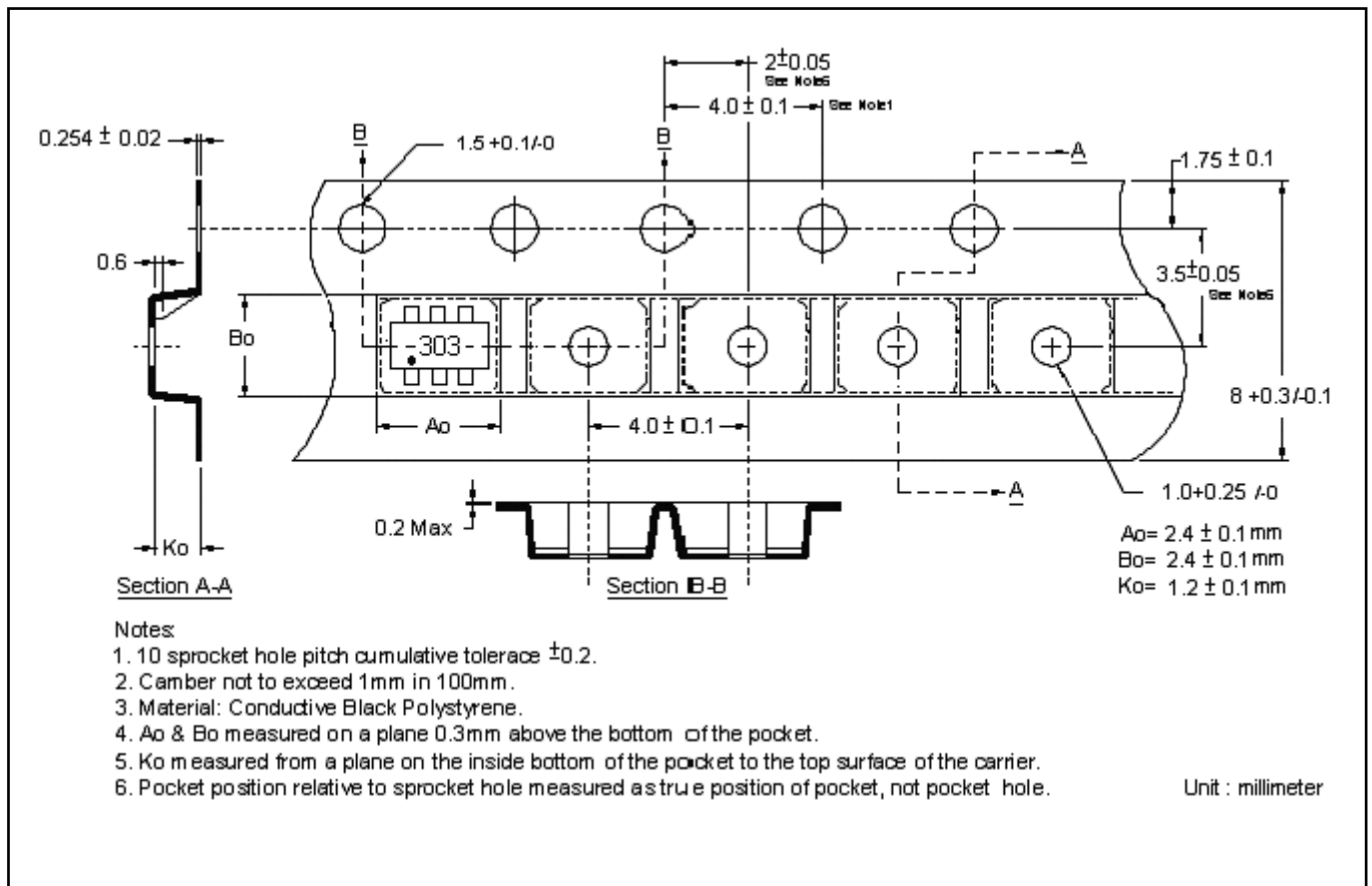
Transient Thermal Response Curves



Reel Dimension



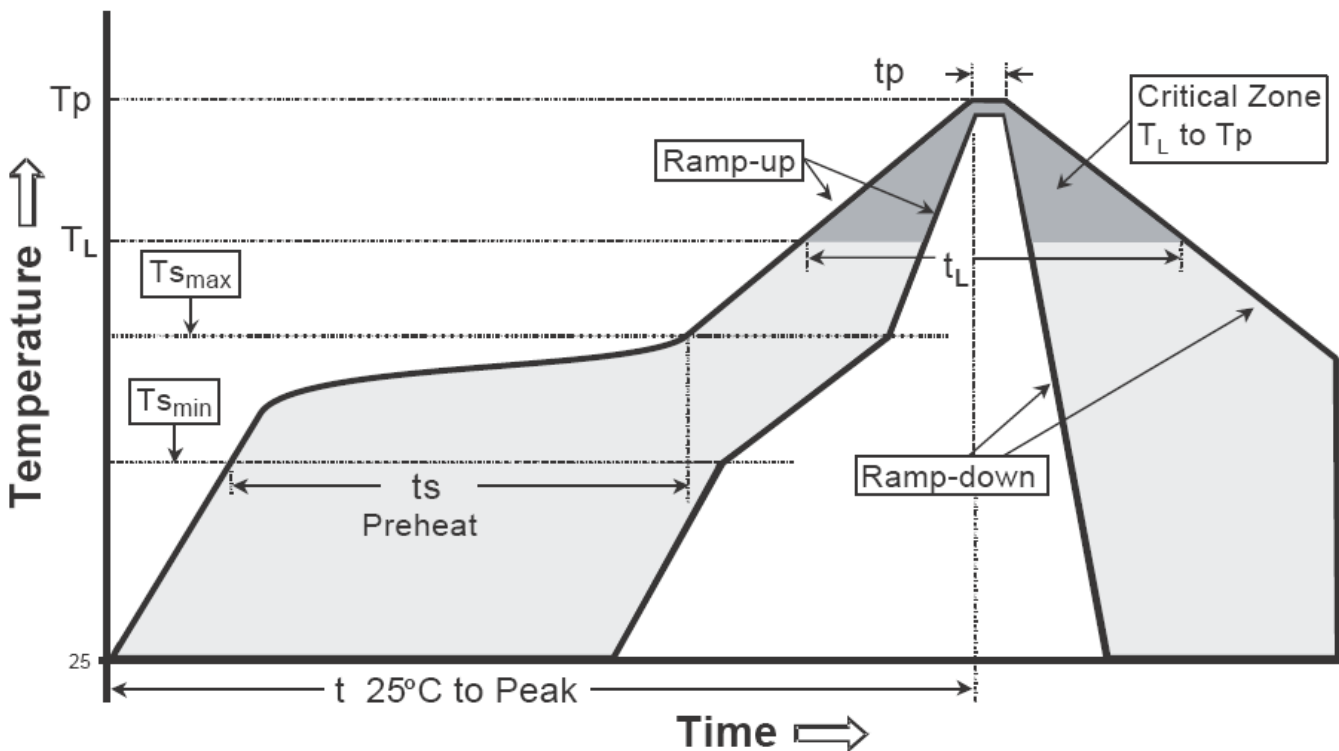
Carrier Tape Dimension



Recommended wave soldering condition

Product	Peak Temperature	Soldering Time
Pb-free devices	260 +0/-5 °C	5 +1/-1 seconds

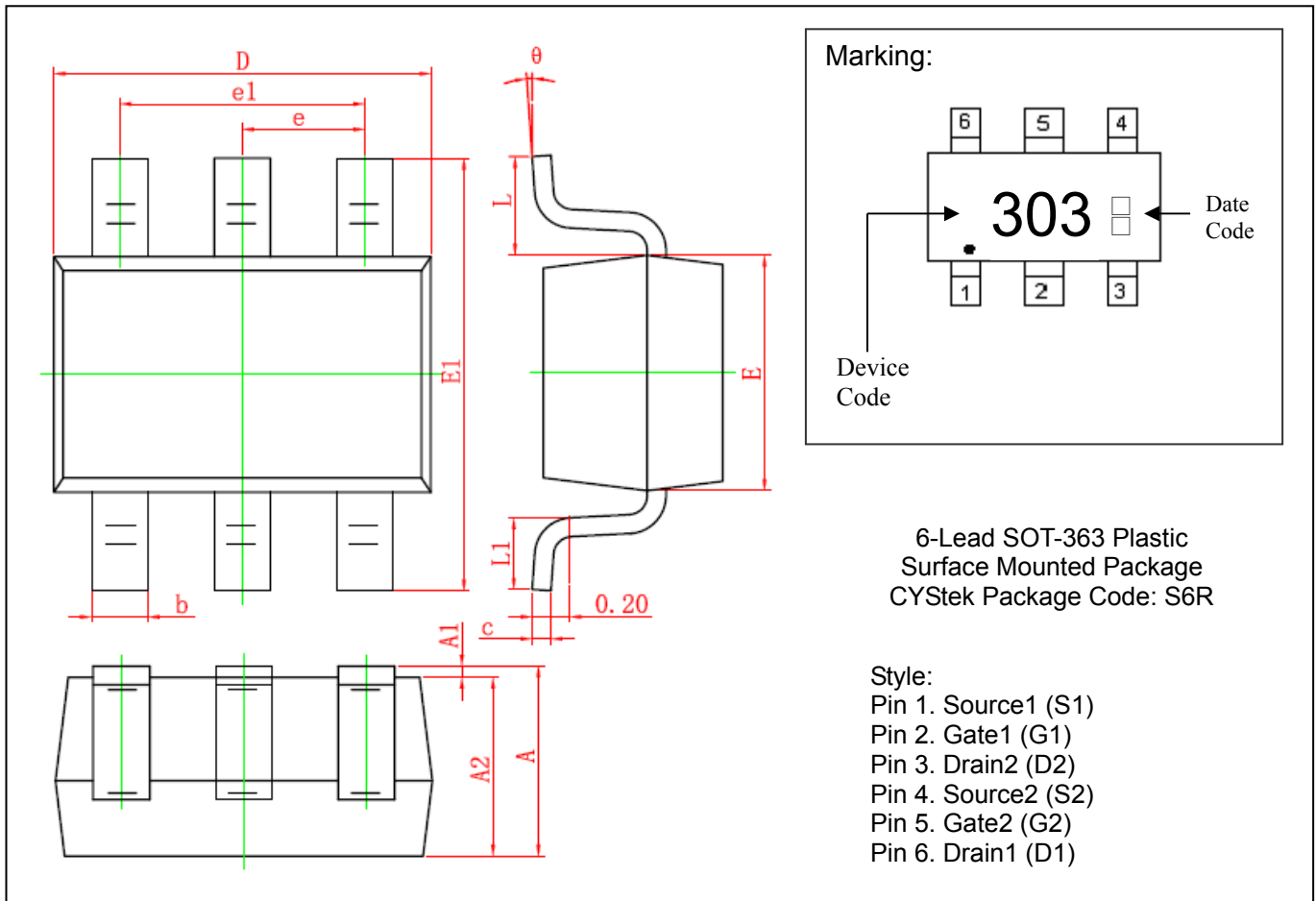
Recommended temperature profile for IR reflow



Profile feature	Sn-Pb eutectic Assembly	Pb-free Assembly
Average ramp-up rate (Tsmax to Tp)	3°C/second max.	3°C/second max.
Preheat		
-Temperature Min(Ts min)	100°C	150°C
-Temperature Max(Ts max)	150°C	200°C
-Time(ts min to ts max)	60-120 seconds	60-180 seconds
Time maintained above:		
-Temperature (T _L)	183°C	217°C
- Time (t _L)	60-150 seconds	60-150 seconds
Peak Temperature(T _P)	240 +0/-5 °C	260 +0/-5 °C
Time within 5°C of actual peak temperature(tp)	10-30 seconds	20-40 seconds
Ramp down rate	6°C/second max.	6°C/second max.
Time 25 °C to peak temperature	6 minutes max.	8 minutes max.

Note : All temperatures refer to topside of the package, measured on the package body surface.

SOT-363 Dimension



DIM	Millimeters		Inches		DIM	Millimeters		Inches	
	Min.	Max.	Min.	Max.		Min.	Max.	Min.	Max.
A	0.900	1.100	0.035	0.043	E1	2.150	2.450	0.085	0.096
A1	0.000	0.100	0.000	0.004	e	0.650	TYP	0.026	TYP
A2	0.900	1.000	0.035	0.039	e1	1.200	1.400	0.047	0.055
b	0.150	0.350	0.006	0.014	L	0.525	REF	0.021	REF
c	0.080	0.150	0.003	0.006	L1	0.260	0.460	0.010	0.018
D	2.000	2.200	0.079	0.087	θ	0°	8°	0°	8°
E	1.150	1.350	0.045	0.053					

Notes : 1.Controlling dimension : millimeters.
 2.Maximum lead thickness includes lead finish thickness, and minimum lead thickness is the minimum thickness of base material.
 3.If there is any question with packing specification or packing method, please contact your local CYStek sales office.

Material :

- Lead : Pure tin plated.
- Mold Compound : Epoxy resin family, flammability solid burning class:UL94V-0.

Important Notice:

- All rights are reserved. Reproduction in whole or in part is prohibited without the prior written approval of CYStek.
- CYStek reserves the right to make changes to its products without notice.
- CYStek **semiconductor products are not warranted to be suitable for use in Life-Support Applications, or systems.**
- CYStek assumes no liability for any consequence of customer product design, infringement of patents, or application assistance.